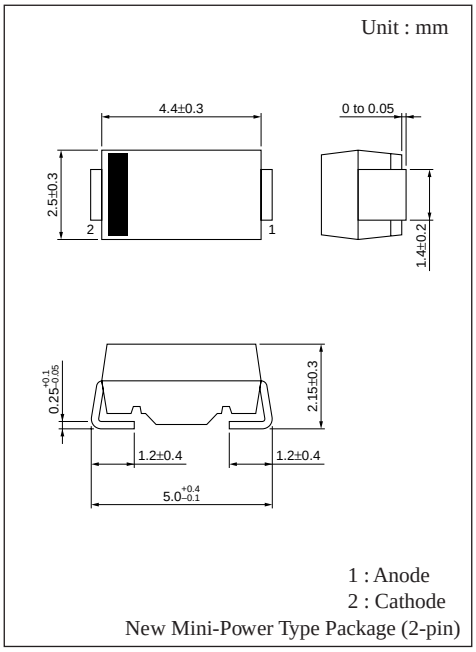
MA736

Silicon epitaxial planer type

For high-frequency rectification

■ Features

- Forward current (average) $I_{F(AV)}$: 1A type
- Reverse voltage (DC value) V_R : 40V
- Automatic insertion possible with emboss taping



Marking Symbol : PB

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Repetitive peak reverse voltage	V_{RRM}	40	V
Average forward current	$I_{F(AV)}$*1	1	A
Non-repetitive peak forward surge current	I_{FSM}*2	30	A
Junction temperature	T_j	– 40 to +125	˚C
Storage temperature	T_{stg}	– 40 to +125	˚C

*1 With a printed-circuit board (copper foil area 2mm × 2mm or more on both cathode and anode sides)

*2 50Hz sine wave, one-cycle wave, high value (non-repetitive)

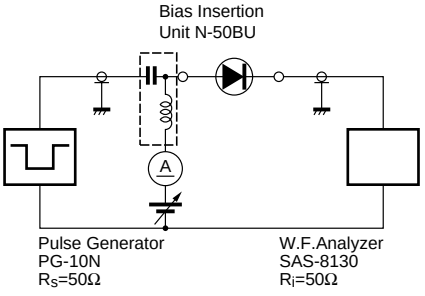
■ Electrical Characteristics (Ta= 25˚C)

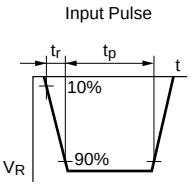
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R = 40V			2	mA
Forward voltage (DC)	V_F	I_F =1A			0.55	V
Terminal capacitance	C_t	V_R =10V, f=1MHz		50		pF
Reverse recovery time	t_{rr}*	I_F = I_R=100mA I_{rr}=10mA, R_L=100Ω			30	ns

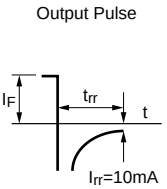
Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

2. Rated input/output frequency : 20MHz

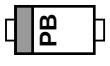
3. * t_{rr} measuring circuit



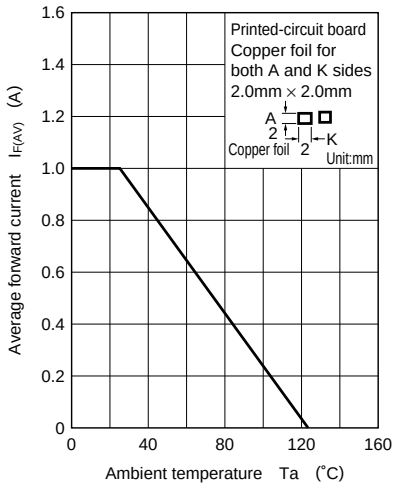




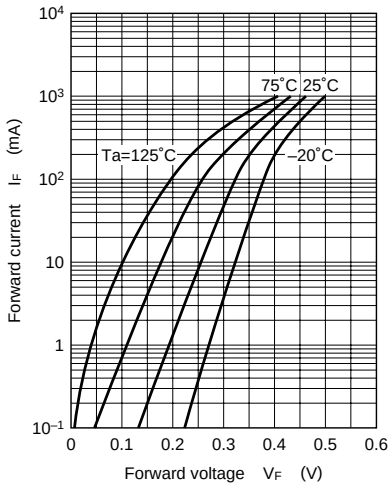
■ Marking



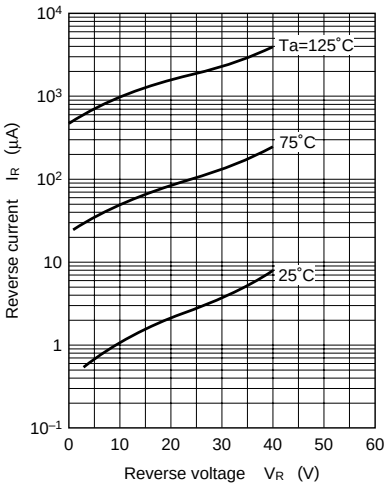
$I_{F(AV)} - Ta$



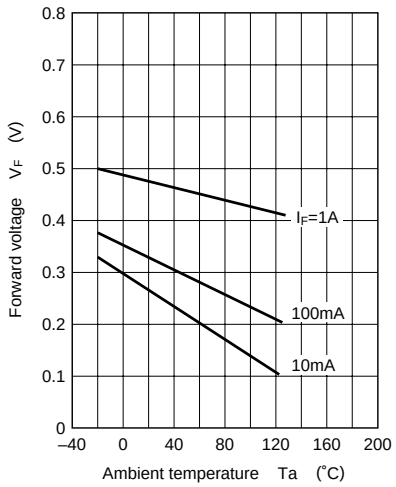
$I_F - V_F$



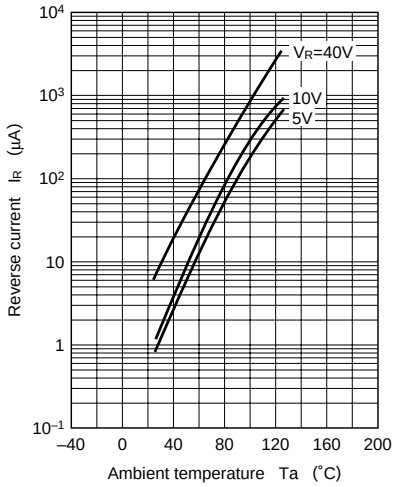
$I_R - V_R$



$V_F - Ta$



$I_R - Ta$



$C_t - V_R$